

AMENDMENTS TO THE SPECIFICATION

Please replace paragraphs [0032] and [0033] with the following amended paragraphs:

[0032] The first SiO_xN_y layer 120 is a tensile-stress layer on the substrate 110. The first SiO_xN_y layer 120 is deposited by a PECVD process. The PECVD process usually uses a low pressure and a low power. The x value usually ranges from 0 to 2. The y value usually ranges from 0 to 4/3. The thickness of the first SiO_xN_y layer 120 ranges, for example, from 5 μm to 35 μm . For instance, the first SiO_xN_y layer [[130]] 120 has a thickness approximately equal to 20 micron. The tensile stress of the first SiO_xN_y layer [[130]] 120 is usually low and may range from 0.01 MPa to 1 MPa. For example, the tensile stress equals approximately 0.5 MPa.

[0033] The second SiO_xN_y layer 130 is a compressive-stress layer on the first SiO_xN_y layer 120. The second SiO_xN_y layer 130 is deposited by a PECVD process. The PECVD process usually uses a high pressure and a high power. The x value usually ranges from 0 to 2. The y value usually ranges from 0 to 4/3. The thickness of the second SiO_xN_y layer 130 ranges, for example, from 0.5 μm to 5 μm . For instance, the second SiO_xN_y layer 130 has a thickness approximately equal to 2.5 micron. The compressive stress of the second SiO_xN_y layer 130 may range from 1 MPa to 100 MPa. For example, the tensile compressive stress equals approximately 20 MPa.